



Semefab

Sensor and Silicon Solutions

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Semefab Overview

- ❑ Custom Wafer Fabrication
 - ❑ Ship ~115 million Dies / year
 - ❑ Development Model
 - Full Technology Cycle
 - ❑ Volume Model
 - ❑ Design Partnerships
 - ❑ Technology Transfers
 - ❑ Established 1986
 - ❑ Private Ownership
- ❖ ~£7M turnover (FY08)
 - ❖ Global Fabrication Player
 - ❖ ~64% Export Bias
 - ❖ >35 Customers Worldwide
 - ❖ £13.6M Capex Investment
- Fab 1: 2.0 μ m - 3.0 μ m
 - Fab 2: 0.45 μ m
 - Fab 3: 0.45 μ m

Manufacturing Operations

Fab Operations

- ❑ Fab 1: 4" Multi-Process
- ❑ Fab 2: 4" & 6" MEMS
- ❑ Fab 3: 6" Multi-Process
- ❑ Wafer Test Operation
- ❑ ISO9001, ISO14001, BS5750
- ❑ UL & ESA Approval
- ❑ Investors in People
- ❑ Team of 98 People
 - 2% Doctorate
 - 7% Masters
 - 12% Graduate
 - 15% Technicians

Diverse Process Portfolio

- ❑ Si Gate CMOS & Opto CMOS
- ❑ Metal Gate CMOS & PMOS
- ❑ HV DI BiCMOS
- ❑ Mixed Signal ASICs & Opto ASICs
- ❑ Linear Bipolar & Epitaxial Bipolar
- ❑ Discrete DMOS RF MOSFET
- ❑ Discrete Lateral FET
- ❑ Discrete Low Noise N Channel JFET
- ❑ Discrete P Channel MOSFET
- ❑ Discrete PiN Photo Diode
- ❑ Power MOS
- ❑ Power Bipolar
- ❑ Fast Recovery Diode
- ❑ MEMS

Development Model

- ❑ Open Access Facility for Industry and Academia
 - *Technology Partnering*
 - *Background & Foreground IP agreements*
- ❑ Full Technology Cycle - *Feasibility - Proof of Concept - Prototypes*
- ❑ Commercialisation Focus
 - *Tangible Development Outcomes*
 - *Funding Justification - Research, Venture Capital, Investor...*
- ❑ In-house Design Simulation & External Partnerships
- ❑ Semefab Process Development & Process Engineering Integration
- ❑ Seamless Transition from Development to Volume
- ❑ In-house Test Operation for product development

Volume Model

- ❑ Fab 1: Fabrication capacity of 50,000 4" wafers per year
- ❑ Fab 2: Fabrication capacity of 25,000 4" /6" wafers per year
- ❑ Test floor supports wafer test & package test
 - *Electrical parametric testing*
 - *Sensor functional testing i.e. pressure etc.*
 - *Actual device packaging is subcontracted*
- ❑ Fab 3: Planning 25,000 6" wafers volume per year
 - *Fab3 design phase starts September 2009*
 - *Fab 3 scheduled operational date June 2010*
- ❑ Semefab is your low risk, value-add fabrication partner

Diverse Portfolio

ASIC Portfolio:

- Garage Door Opener
- JFET PIR Sensor
- Ionisation Smoke Detector
- Optical Smoke Detector
- Automotive Wiper
- Automotive Window Lift
- PSU Watchdog
- Light Sensing & Switching

Foundry Portfolio:

- Precision Op-Amps
- Mains Borne Signalling
- Secure Telecoms
- RF Base Stations & PMR
- Audio Amplification
- Power Devices & Modules
- X-Ray Detection

MEMS Portfolio:

- Pollution Control
- Automotive Engine Mgt
- Automotive Air Quality
- Altimeters
- Ear Thermometers
- Optical Transceiver
- Pressure Sensors
- Gas Sensors
- Temperature Sensors

MEMS Development: > 22 Active Development Projects

Fab1 Process Capability

- Double Side Alignment
- Wet Etch - Pre-diff clean, HF, HCl, Buffered oxide etch, Al wet etch, Si Etch, Hot Orthophosphoric etch, Solvent Strip, Overlay etch
- Dry Etch - PolySi, SiO₂, Nitride, Aluminium
- PECVD Low stress Nitride & Oxynitride
- PECVD TEOS & BPTEOS
- Furnace Stacks - LPCVD Nitride, Poly, Oxide
- Furnace Stacks - Thermal Oxidation, Diffusion, Boron & Phos Doping
- Ion Implant
- Sputter - AlSi, Al, Cu

Fab2 Layout



600m²

Class 100

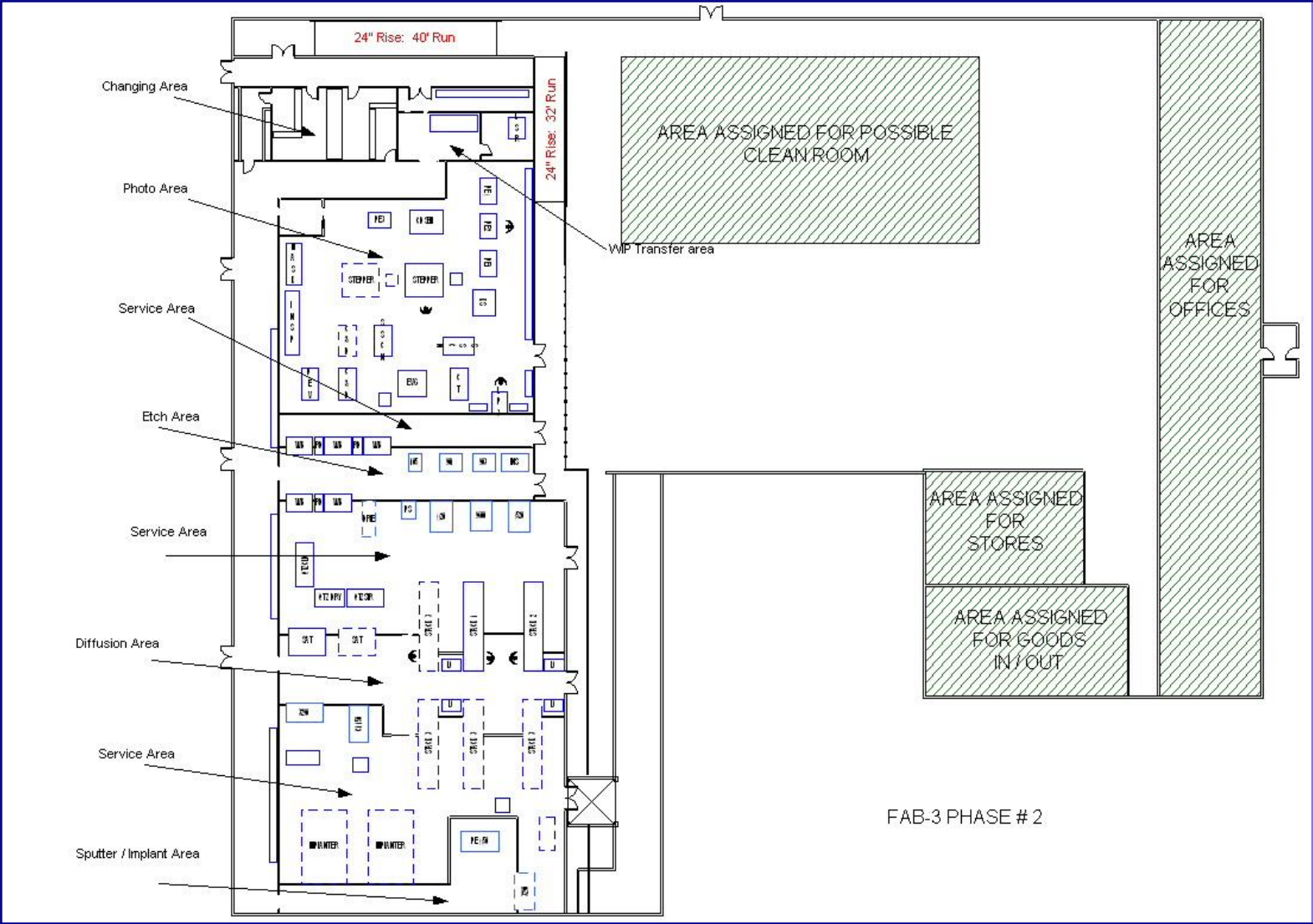
Photo is class 10

Central corridor is
class 1000

Fab2 Process Capability

- Oxidation Stack
- Wet Etch - Pre-diff clean, HF, HCl, Buffered oxide etch, Al wet etch, Si Etch, Solvent Strip
- KOH wet etch, Lift-off
- Multi-Metal Sputter - Au, TiW, Al, AlSi, AlCu, Ti, Ni, NiCr, Al₂O₃, Constantan, SiCr, Sn
- Evaporation - Cr, Ni, Pt, Au, Ti
- Dry Etch - Oxide, Poly/Nitride
- Double side aligner
- Stepper
- PECVD Thin Films - SiO₂, SiN, SiON
- Wafer-Wafer & Wafer-Glass Bonding Anodic, Eutectic, Fusion, Glass-Frit
- Coat/Develop track - bulk dispense
- Coat/Develop track - syringe dispense
- Polyimide - coat & bake
- XeF₂ dry etch release
- HF vapour dry etch release
- Deep Reactive Ion Etch (Fab1 Annexe) *STS Pegasus*
- Electroplating of Cu and Au
- Resist strip dry etch

Fab3 Layout



1,200m² Class 100

Fab3 Planned Process Capability

- Furnace stack - LPCVD Oxide, Poly, Nitride
- Furnace stack - Oxidation, Drive, Boron & Phos Deposition
- Double side aligner
- Stepper
- Wet etch
- Dry etch - Oxide, Poly/Nitride, Metal etch
LAM Rainbow platform
- Sputter - Al, AlSi, AlCu with pre-etch



Test Operations Capability

- ❑ Reedholm Instruments RI20/RI40 Parametric Tester(3)
- ❑ Tesec 8101TT - Discrete Device Tester (3kV/20A) (1)
- ❑ Exatron SOIC / DIP Handler (2)
- ❑ Multitest SOIC / DIP Handler -400C to +1250C (5)
- ❑ Electroglas 2001X Wafer Auto-prober (6)
- ❑ Wentworth 1050 Semi-auto Prober (high-voltage) (1)

Thank you - Any Questions?



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